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July 2016

## FFSP3065A

# Silicon Carbide Schottky Diode 650 V, 30 A

#### **Features**

- Max Junction Temperature 175 °C
- · Avalanche Rated 180 mJ
- · High Surge Current Capacity
- · Positive Temperature Coefficient
- · Ease of Paralleling
- No Reverse Recovery / No Forward Recovery

## **Applications**

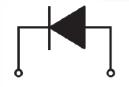
- General Purpose
- SMPS, Solar Inverter, UPS
- · Power Switching Circuits

## **Description**

SiC Schottky Diode has no switching loss, provides improved system efficiency against Si diodes by utilizing new semiconductor material - Silicon Carbide, enables higher operating frequency, and helps increasing power density and reduction of system size/cost. Its high reliability ensures robust operation during surge or over-voltage conditions

2. Anode





1. Cathode

### Absolute Maximum Ratings T<sub>C</sub> = 25 °C unless otherwise noted.

Symbol	Parameter		FFSP3065A	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 1)	180	mJ
IF	Continuous Rectified Forward Current @ T <sub>C</sub> < 148 °C		30	Α
	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25 °C, 10 μs	1125	А
IF, Max		T <sub>C</sub> = 150 °C, 10 μs	1040	Α
I <sub>F,SM</sub>	Non-RepetitiveForwardSurgeCurrent	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	150	Α
I <sub>F,RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	75	Α
Ptot	Dower Dissination	T <sub>C</sub> = 25 °C	240	W
	Power Dissipation	T <sub>C</sub> = 150 °C	40	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C

#### **Thermal Characteristics**

Symbol	Parameter	FFSP3065A	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.62	°C/W

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSP3065A	FFSP3065A	TO-220-2L	Tube	N/A	N/A	50 units

## **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
		$I_F = 30 \text{ A}, T_C = 25  ^{\circ}\text{C}$	-	1.50	1.75	
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 30 A, T <sub>C</sub> = 125 °C	-	1.60	2.0	V
		I <sub>F</sub> = 30 A, T <sub>C</sub> = 175 °C	-	1.72	2.4	
I <sub>R</sub>	Reverse Current	$VR = 650 \text{ V}, T_C = 25 ^{\circ}\text{C}$	-	-	200	μА
		$VR = 650 \text{ V}, T_C = 125  ^{\circ}\text{C}$	-	-	400	
		$VR = 650 \text{ V}, T_C = 175  ^{\circ}\text{C}$	-	-	600	
Q <sub>C</sub>	Total Capacitive Charge	V = 400 V	-	100	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	1705	-	pF
		V <sub>R</sub> = 200 V, f = 100 kHz	-	180	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	-	130	-	

Notes: 1: EAS of 180 mJ is based on starting  $T_J$  = 25 °C, L = 0.5 mH,  $I_{AS}$  = 27 A, V = 50 V.

## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

Figure 1. Forward Characteristics

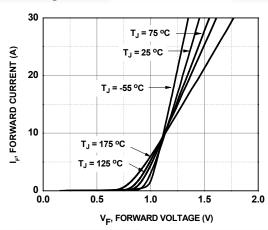


Figure 3. Current Derating

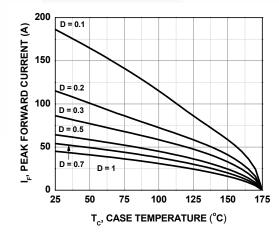


Figure 2. Reverse Characteristics

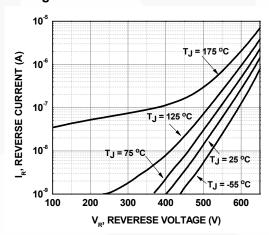
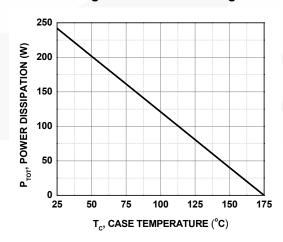


Figure 4. Power Derating



## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted.

Figure 5. Capacitive Charge vs. Reverse Voltage

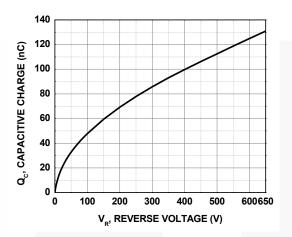


Figure 6. Capacitance vs. Reverse Voltage

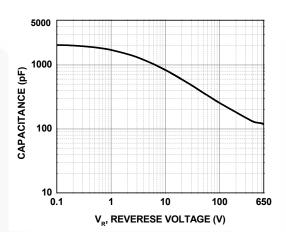


Figure 7. Capacitance Stored Energy

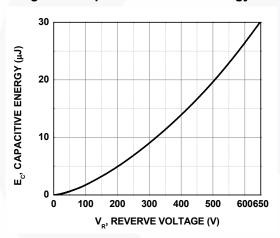
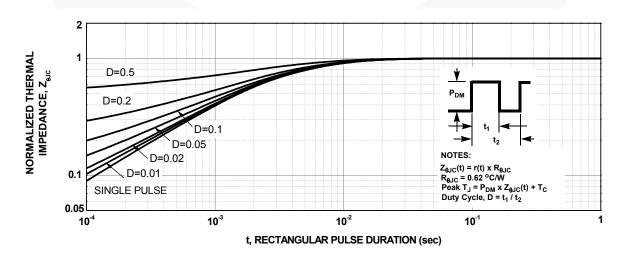
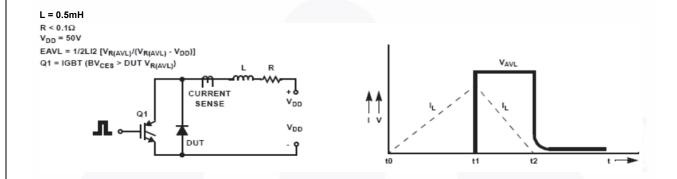


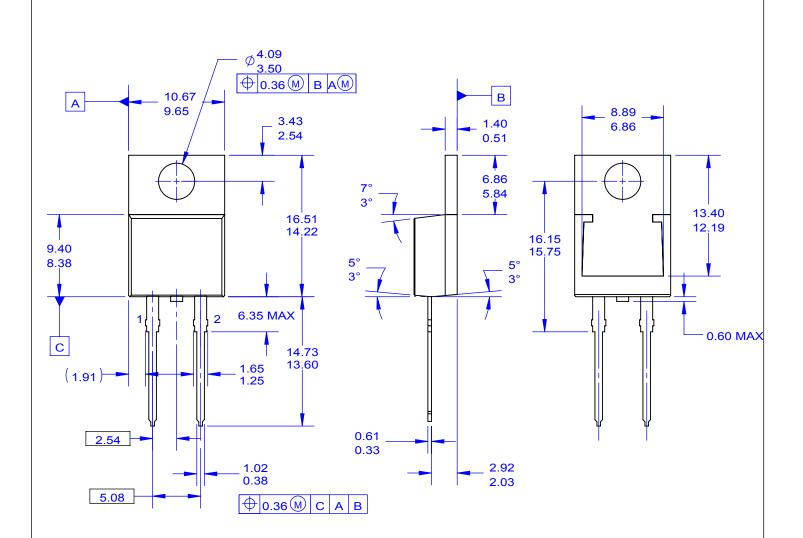
Figure 8. Junction-to-Case Transient Thermal Response Curve

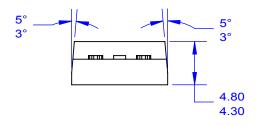


## **Test Circuit and Waveforms**

Figure 9. Unclamped Inductive Switching Test Circuit & Waveform









#### **NOTES:**

- A. PACKAGE REFERENCE: JEDEC TO220,ISSUE K, VARIATION AC,DATED APRIL 2002.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
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